

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4330PA.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-30	V
I _C	collector current			-	-	-3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-5	А
R _{CEsat}	collector-emitter saturation resistance	I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	75	107	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	E	emitter		1
3	С	collector		2
				sym013
			Transparent top view DFN2020-3 (SOT1061)	

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS5330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061		

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5330PA	AJ

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8. Limiting values

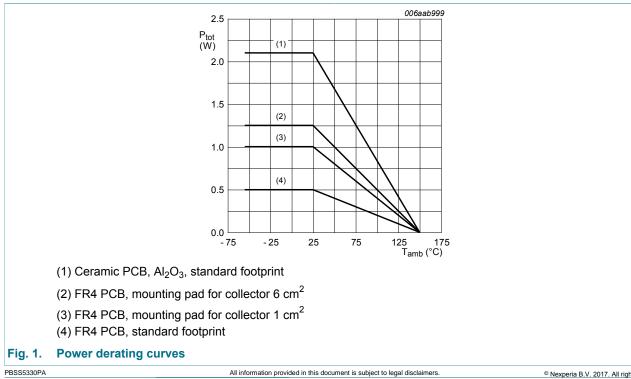
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-30	V
V _{CEO}	collector-emitter voltage	open base		-	-30	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	А
I _B	base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

- ^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- ^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.



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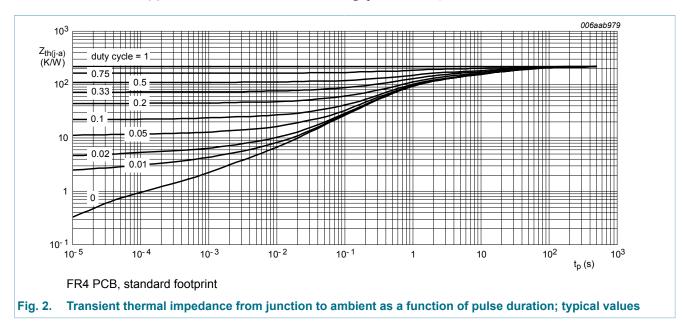
9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W	
		[2]	-	-	125	K/W	
		[3]	-	-	100	K/W	
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

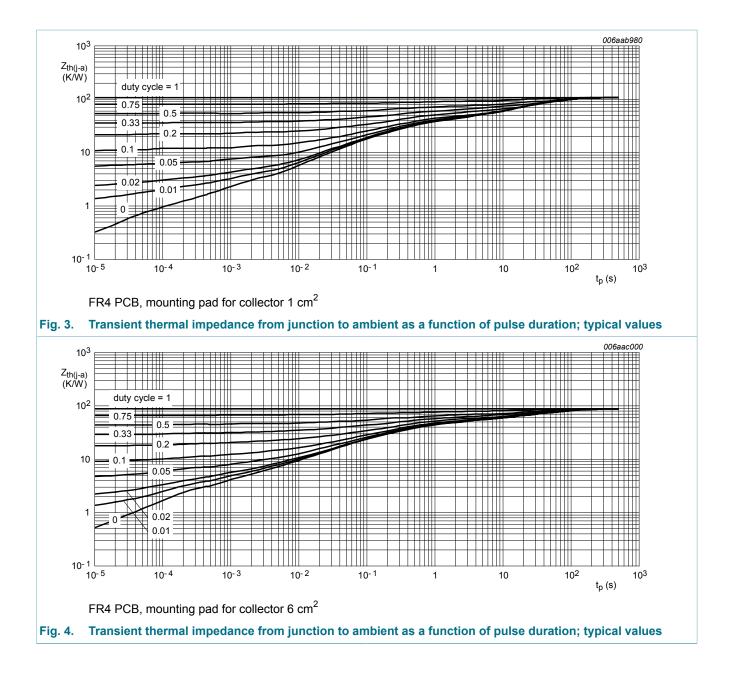
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.





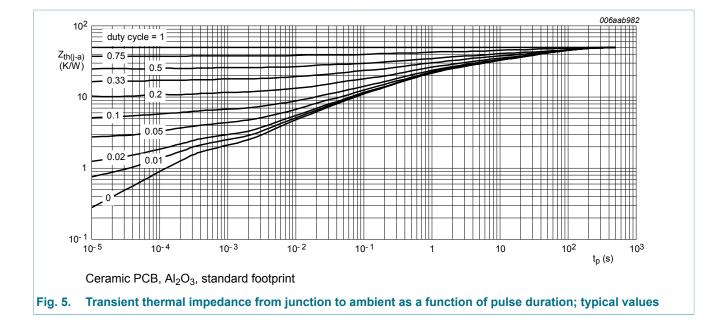
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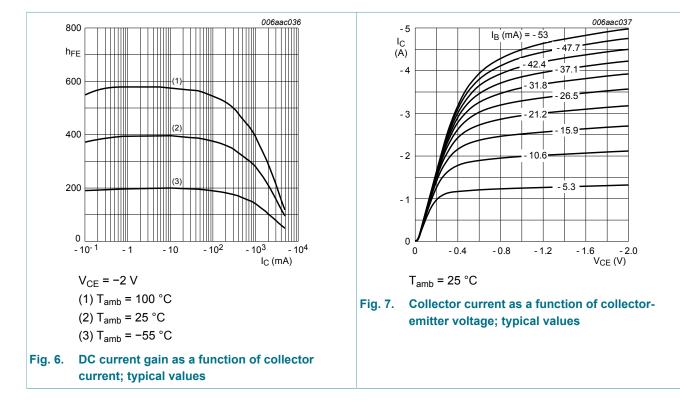
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
current		V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -24 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$\begin{split} &V_{CE} \texttt{=-2 V; I}_{C} \texttt{=-0.5 A; pulsed;} \\ &t_{p} \texttt{\leq 300 } \mu\texttt{s; } \delta \texttt{\leq 0.02 }; T_{amb} \texttt{= 25 }^{\circ}C \end{split}$	200	320	-	
		$\begin{split} V_{CE} &= -2 \text{ V; } \text{I}_{C} = -1 \text{ A; pulsed;} \\ t_{p} &\leq 300 \mu\text{s; } \delta \leq 0.02 \text{; } T_{amb} = 25 ^{\circ}\text{C} \end{split}$	175	280	450	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	140	210	-	
	V_{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	100	160	-		
V _{CEsat} collector-emitter saturation voltage	I_{C} = -0.5 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-45	-70	mV	
		I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-90	-130	mV
		$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-170	-240	mV
		I_{C} = -3 A; I_{B} = -300 mA; pulsed;	-	-230	-320	mV
R _{CEsat}	collector-emitter saturation resistance	$t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb} = 25 \ ^\circ C$	-	75	107	mΩ
V _{BEsat}	base-emitter saturation voltage	$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-0.89	-1.1	V
		$\begin{split} I_C &= -3 \text{ A}; I_B = -300 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^\circ\text{C} \end{split}$	-	-0.97	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.75	-1	V
t _d	delay time	V _{CC} = -9 V; I _C = -2 A; I _{Bon} = -0.1 A;	-	11	-	ns
t _r	rise time	I _{Boff} = 0.1 A; T _{amb} = 25 °C	-	59	-	ns
t _{on}	turn-on time		-	70	-	ns
t _s	storage time		-	165	-	ns
t _f	fall time		-	35	-	ns
t _{off}	turn-off time	-	-	200	-	ns

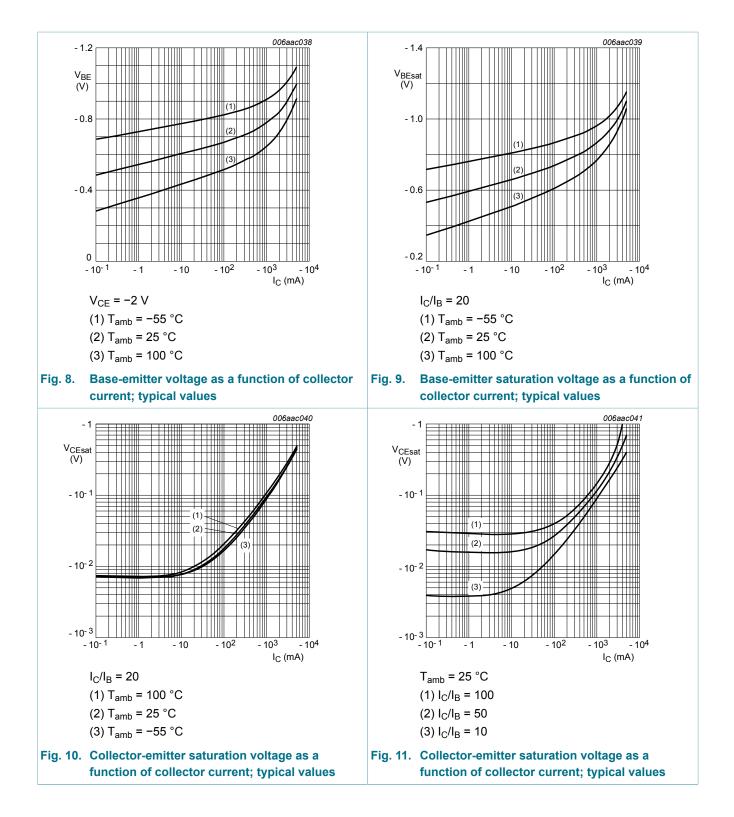
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = -5 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	100	165	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	38	45	pF



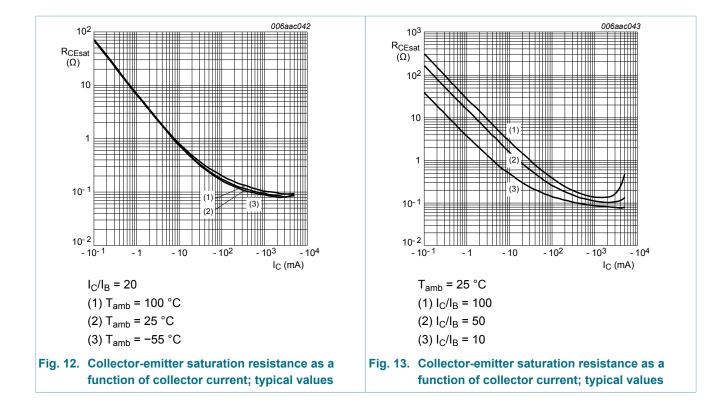
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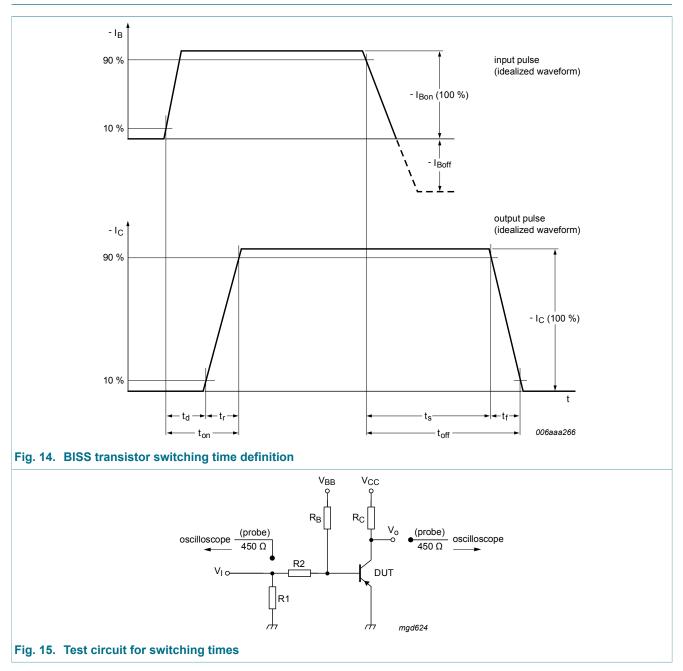
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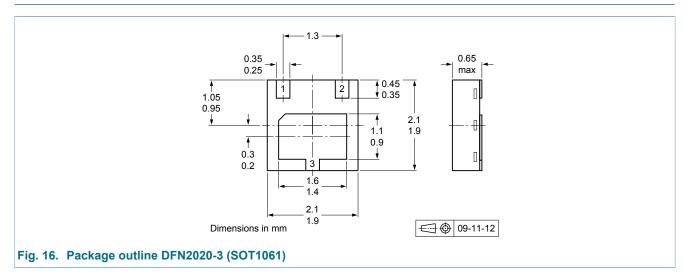
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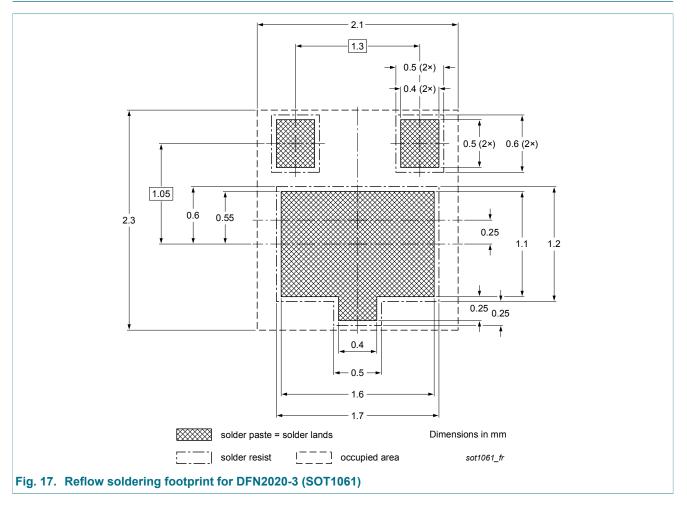
11. Test information

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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5330PA v.2	20150407	Product data sheet	-	PBSS5330PA v.1
Modifications: • Condition V _{CE} changed for parameter I _{CES} in Table 7, Characteristics				
PBSS5330PA v.1	20100419	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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